## **Supporting Information**

## Strong Addition Effect of n-type Polymer with Mid-Energy Level in Polymer:Fullerene Solar Cells with Power Conversion Efficiency Exceeding 10%

Hyemi Han,<sup>†a</sup> Jooyeok Seo,<sup>†a</sup> Myeonghun Song,<sup>a</sup> Hwajeong Kim,<sup>\*ab</sup> and Youngkyoo Kim<sup>\*a</sup>

- <sup>a.</sup> Organic Nanoelectronics Laboratory and KNU Institute for Nanophotonics Applications (KINPA), Department of Chemical Engineering, School of Applied Chemical Engineering, Kyungpook National University, Daegu 41566, Republic of Korea
- <sup>b.</sup> Priority Research Center, Research Institute of Advanced Energy Technology, Kyungpook National University, Daegu 41566, Republic of Korea

\*Corresponding authors: Email) ykimm@knu.ac.kr, khj217@knu.ac.kr; Tel) +82-53-950-5616

<sup>†</sup>These authors contributed equally to this work.

| Authors<br>(Affiliation)                             | Polymer<br>Additive <sup>*</sup> | Device Structure   | Features &<br>Energy Band Diagrams   | PCE (%) | Year | Ref |
|--|----------------------------------|--|--|---------|------|-----|
| R. Lin, et al.<br>(U. New South<br>Wales, Australia) | PTB7                             | ITO/ZnO/PTB7:PCPDT<br>BT:PC71BM/MoO3/Ag                        | <ul> <li>Electron-donating polymer</li> <li>NOT mid-energy level additive (close to an electron donor)</li> <li>Amount: 5 wt%</li> <li>4.4 4.3 5 3.55 3.31 5 4.6 Ag</li> <li>4.7 10 0 0 0 5 5.1 5.1 5.1 5.1</li> </ul>   | 4.28    | 2014 | 34  |
| CY. Chi, et al.<br>(NTUST, Taiwan)                   | THC8                             | ITO/ZnO/P3HT:THC8:<br>PC <sub>61</sub> BM/MoO <sub>3</sub> /Ag | <ul> <li>Bifunctional copolymer</li> <li>NOT mid-energy level additive (close to an electron donor)</li> <li>Amount: 0.15 wt%</li> <li> <sup>2,9</sup> <sup>2,7</sup> <sup>2,7</sup> <sup>2,9</sup> <sup>2,7</sup> <sup>2,9</sup> <sup>2,7</sup> <sup>2,7</sup> <sup>2,7</sup> <sup>2,7</sup> <sup>2,8</sup> <sup>2,3</sup> <sup>2,7</sup> <sup>2,6</sup> <sup>2,7</sup> <sup>2,7</sup></li></ul> | 3.88    | 2014 | 37  |
| This work  | THBT-ht                          | ITO/ZnO/PTB7-Th:<br>THBT-ht:PC71BM/MoO3<br>/Ag                 | •Electron-accepting polymer<br>•Mid-energy level additive<br>•Amount: 0.5 wt%<br>4.3 $4.2$ $3.9$ $4.7$ $4.3$ $4.2$ $3.9$ $4.7$ $4.9$ $4.3$ $4.2$ $5.2$ $5.3$ $4.7$ $4.9$ $5.7$ $5.2$ $5.3$ $4.7$ $4.9$ $5.7$ $5.2$ $5.3$ $4.7$ $4.9$ $5.7$ $5.2$ $5.3$ $5.7$   | 10.02   | 2017 | -   |

Table S1. Summary of recent reports on the inverted-type polymer:fullerene solar cells with conjugated polymer additives. Note that both minus (-) sign and energy unit (eV) in the energy band diagrams are omitted.

\*Full names of the polymer additives:

- PTB7: Poly[[4.8-bis[(2-ethylhexyl)oxy]benzo[1,2-b:4,5-b']dithiophene-2,6-diyl][3-fluoro-2-[(2-ethylhexyl)carbonyl]thieno[3,4 b]thio-phenediyl]

THC8: Not provided from original paper (Unit names are only given) (see ref. 37)
THBT-ht: Poly(3-hexyltiophene-*co*-benzothiadiazole) end-capped with hexylthiophene



**Fig. S1.** (a) PL spectra for the binary blend (PTB7-Th:THBT-ht) films coated on the quartz substrates (excitation wavelength = 640 nm). (b) PL peak intensity as a function of the THBT-ht content for the binary blend (PTB7-Th:THBT-ht) films.



**Fig. S2.** Optical absorption spectra for the pristine films (PTB7-Th,  $PC_{71}BM$ , and THBT-ht) coated on the quartz substrates. The thickness of each film is given below the name of material.



**Fig. S3.** Current density (J) – applied voltage ( $V_{APP}$ ) characteristics of (a) hole-only devices (HODs) and (b) electron-only devices (EODs): (left) semi-logarithmic scale, (right) full logarithmic scale. The holes in the HODs are transported mainly through the HOMO levels of the PTB7-Th component, while the electrons in the EODs are transported mainly through the LUMO levels of the PC<sub>71</sub>BM component in the presence of marginal contribution by the THBT-th component. Note that the effective voltage obtained by subtracting the built-in voltage from the applied voltage ( $V_{APP}$ ) was used for the calculation of charge carrier mobility using the space-charge limited current (SCLC) model (see the references 43 and 44 in the manuscript).



**Fig. S4.** 2D height-mode AFM images for the BHJ (PTB7-Th:PC<sub>71</sub>BM) layers with the THBT-ht additive, which were coated on the ZnO/ITO-glass substrates: (a) THBT-ht = 0 wt%, (b) 0.25 wt%, (c) 0.5 wt%, (d) 1.0 wt%, (e) 3.0 wt%. The scan size of the AFM images was 3  $\mu$ m × 3  $\mu$ m.



**Fig. S5.** TEM images, which were measured on the different position from Figure 5, for the BHJ (PTB7-Th:PC $_{71}$ BM) films with the THBT-ht additive. The selected-area electron diffraction (SAED) patterns (right) were measured by focusing on the bright (B) and dark (D) parts in the BHJ films.



**Fig. S6.** (a) Photographs for the operation of three different color LEDs (left: red, middle: green, right: blue) by using the semi-solar module made by series connection of four individual inverted-type PTB7-Th:PC<sub>71</sub>BM solar cells with the THBT-ht additive (0.5 wt%). The simulated solar light (air mass 1.5 G, 100 mW/cm<sup>2</sup>) was continuously exposed to the top part of the semi-solar module for 10 h. (b) Video clip for the operation of the semi-solar module under continuous illumination with the simulated solar light for 10 h (filename: video\_clip\_fig. S6b).